



## TPS22965x-Q1 5.5-V, 4-A, 16-mΩ On-Resistance Load Switch

### 1 Features

- Qualified for Automotive Applications
  - AEC-Q100 Qualified
  - Device Temperature Grade 2:  $-40^{\circ}\text{C}$  to  $105^{\circ}\text{C}$  (TPS22965-Q1, TPS22965N-Q1)
  - Device Temperature Grade 1:  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  (TPS22965W-Q1)
  - Device HBM ESD Classification Level 3A
  - Device CDM ESD Classification Level C6
- Integrated Single Channel Load Switch
- Input Voltage Range: 0.8 V to 5.5 V
- Ultra-Low On Resistance ( $R_{\text{ON}}$ )
  - $R_{\text{ON}} = 16\text{ m}\Omega$  at  $V_{\text{IN}} = 5\text{ V}$  ( $V_{\text{BIAS}} = 5\text{ V}$ )
  - $R_{\text{ON}} = 16\text{ m}\Omega$  at  $V_{\text{IN}} = 3.6\text{ V}$  ( $V_{\text{BIAS}} = 5\text{ V}$ )
  - $R_{\text{ON}} = 16\text{ m}\Omega$  at  $V_{\text{IN}} = 1.8\text{ V}$  ( $V_{\text{BIAS}} = 5\text{ V}$ )
- 4 A Maximum Continuous Switch Current
- Low Quiescent Current (50  $\mu\text{A}$ )
- Low Control Input Threshold Enables Use of 1.2-V, 1.8-V, 2.5-V and 3.3-V Logic
- Configurable Rise Time
- Quick Output Discharge (QOD) (TPS22965-Q1 and TPS22965W-Q1 Only)
- SON 8-pin Package with Thermal Pad
- TPS22965W-Q1: Product Preview Only

### 2 Applications

- Automotive Electronics
- Infotainment
- ADAS (Advanced Driver Assistance Systems)

### 3 Description

The TPS22965x-Q1 is a small, ultra-low  $R_{\text{ON}}$ , single channel load switch with controlled turn on. The device contains an N-channel MOSFET that can operate over an input voltage range of 0.8 V to 5.5 V and can support a maximum continuous current of 4 A. The  $V_{\text{OUT}}$  rise time is configurable so that inrush current may be reduced. The TPS22965-Q1 and TPS22965W-Q1 devices include a 225  $\Omega$  on-chip load resistor for quick output discharge when the switch is turned off.

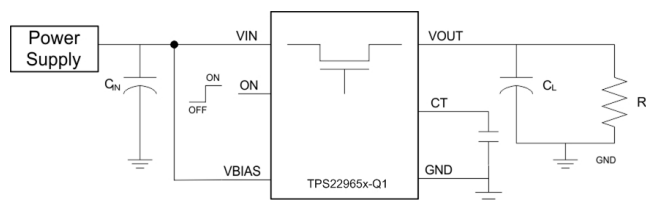
The TPS22965x-Q1 devices are available in a small, space-saving 2.00 mm x 2.00 mm 8-pin SON package (DSG) with integrated thermal pad allowing for high power dissipation. The TPS22965-Q1 and TPS22965N-Q1 devices are characterized for operation over the free-air temperature range of  $-40^{\circ}\text{C}$  to  $105^{\circ}\text{C}$ . Furthermore, the TPS22965W-Q1 device features wettable flanks in the same SON package (DSG) and it is characterized for operation over the free-air temperature range of  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ .

#### Device Information<sup>(1)</sup>

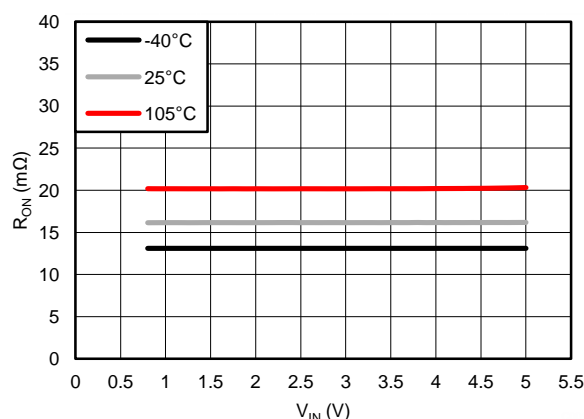
PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS22965x-Q1	SON (8)	2.00 mm x 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### 4 Simplified Schematic



$R_{\text{ON}}$  vs  $V_{\text{IN}}$  ( $V_{\text{BIAS}} = 5\text{ V}$ ,  $I_{\text{OUT}} = -200\text{ mA}$ )



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## 5 Revision History

### Changes from Revision April 2014 (\*) to Revision A

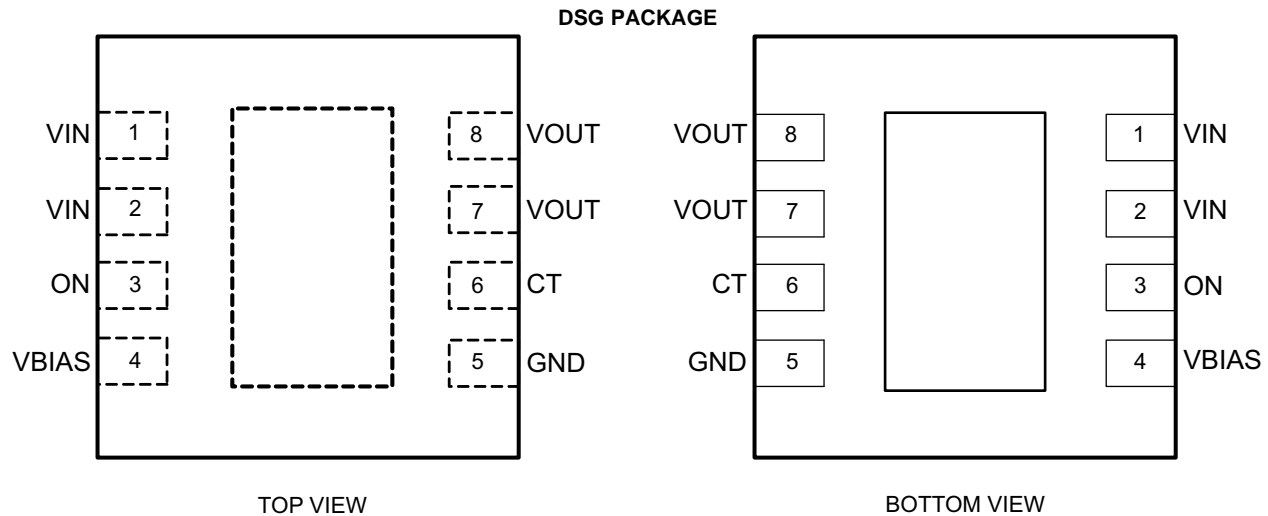
### Page

• Added TPS22965N part number. ....	1
• Updated Thermal Information table. ....	5
• Updated typical AC timing parameters (tables, graphs and scope captures) .....	12

## 6 Device Comparison Table

DEVICE	R <sub>ON</sub> AT 3.3 V (TYP)	STATUS	QUICK OUTPUT DISCHARGE	PACKAGE WITH WETTABLE FLANKS	MAXIMUM OUTPUT CURRENT	TEMPERATURE RANGE
TPS22965-Q1	16 mΩ	ACTIVE	Yes	No	4 A	–40°C to 105°C
TPS22965N-Q1	16 mΩ	ACTIVE	No	No	4 A	–40°C to 105°C
TPS22965W-Q1	16 mΩ	PREVIEW	Yes	Yes	4 A	–40°C to 125°C

## 7 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
VIN	1, 2	I	Switch input. Input bypass capacitor recommended for minimizing V <sub>IN</sub> dip. Must be connected to Pin 1 and Pin 2. See <a href="#">Applications and Implementation</a> for more information.
ON	3	I	Active high switch control input. Do not leave floating.
VBIAS	4	I	Bias voltage. Power supply to the device. Recommended voltage range for this pin is 2.5 V to 5.5 V. See <a href="#">Applications and Implementation</a> for more information.
GND	5	—	Device ground.
CT	6	O	Switch slew rate control. Can be left floating. See <a href="#">Adjustable Rise Time</a> for more information.
VOUT	7, 8	O	Switch output
Thermal Pad	—	—	Thermal pad (exposed center pad) to alleviate thermal stress. Tie to GND. See <a href="#">Layout</a> for layout guidelines.

## 8 Specifications

### 8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> <sup>(2)</sup>

		MIN	MAX	UNIT <sup>(2)</sup>
V <sub>IN</sub>	Input voltage range	–0.3	6	V
V <sub>OUT</sub>	Output voltage range	–0.3	6	V
V <sub>BIAS</sub>	Bias voltage range	–0.3	6	V
V <sub>ON</sub>	On voltage range	–0.3	6	V
I <sub>MAX</sub>	Maximum continuous switch current		4	A
I <sub>PLS</sub>	Maximum pulsed switch current, pulse < 300 μs, 2% duty cycle		6	A
T <sub>J</sub>	Maximum junction temperature		150	°C
T <sub>STG</sub>	Storage temperature range	–65	150	°C

- (1) Stresses beyond those listed under [Absolute Maximum Ratings](#) may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under [Recommended Operating Conditions](#) are not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground pin.

### 8.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

### 8.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>IN</sub>	Input voltage range		0.8	V <sub>BIAS</sub>	V
V <sub>BIAS</sub>	Bias voltage range		2.5	5.5	V
V <sub>ON</sub>	ON voltage range		0	5.5	V
V <sub>OUT</sub>	Output voltage range			V <sub>IN</sub>	V
V <sub>IH</sub>	High-level input voltage, ON	V <sub>BIAS</sub> = 2.5 V to 5.5 V	1.2	5.5	V
V <sub>IL</sub>	Low-level input voltage, ON	V <sub>BIAS</sub> = 2.5 V to 5.5 V	0	0.5	V
C <sub>IN</sub>	Input capacitor		1 <sup>(1)</sup>		μF
T <sub>A</sub>	Operating free-air temperature <sup>(2)</sup>	TPS22965N-Q1, TPS22965-Q1	–40	105	°C
		TPS22965W-Q1	–40	125	

(1) Refer to the [Applications and Implementation](#) section.

(2) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature [T<sub>A(max)</sub>] is dependent on the maximum operating junction temperature [T<sub>J(max)</sub>], the maximum power dissipation of the device in the application [P<sub>D(max)</sub>], and the junction-to-ambient thermal resistance of the part/package in the application (θ<sub>JA</sub>), as given by the following equation: T<sub>A(max)</sub> = T<sub>J(max)</sub> – (θ<sub>JA</sub> × P<sub>D(max)</sub>)

### 8.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS22965-Q1/TPS22965N-Q1	TPS22965W-Q1	UNIT
		DSG (SON)	DSG (SON)	
		8 PINS	8 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	72.3	67.6	°C/W
R <sub>θJCTop</sub>	Junction-to-case (top) thermal resistance	96.1	95	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	42.1	37.4	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	3.3	2.9	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	42.5	37.7	°C/W
R <sub>θJCbott</sub>	Junction-to-case (bottom) thermal resistance	13.2	8	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

**TPS22965-Q1**

SLVSCI3A – APRIL 2014 – REVISED JUNE 2015

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## 8.5 Electrical Characteristics

Unless otherwise note, the specification in the following table applies over the operating ambient temperature  $-40^{\circ}\text{C} \leq T_A \leq 105^{\circ}\text{C}$  (TPS22965N-Q1, TPS22965-Q1),  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$  (TPS22965W-Q1) and  $V_{\text{BIAS}} = 5.0\text{ V}$ . Typical values are for  $T_A = 25^{\circ}\text{C}$ .

PARAMETER		TEST CONDITIONS		T <sub>A</sub>	MIN	TYP	MAX	UNIT
POWER SUPPLIES AND CURRENTS								
I <sub>Q</sub> V <sub>BIAS</sub>	V <sub>BIAS</sub> quiescent current	I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = V <sub>ON</sub> = V <sub>BIAS</sub> = 5.0 V		−40°C to 105°C	50	75	μA	
				−40°C to 125°C	50	75		
I <sub>SD</sub> V <sub>BIAS</sub>	V <sub>BIAS</sub> shutdown current	V <sub>ON</sub> = GND, V <sub>OUT</sub> = 0 V		−40°C to 105°C		2	μA	
				−40°C to 125°C		2		
I <sub>SD</sub> V <sub>IN</sub>	V <sub>IN</sub> off-state supply current	V <sub>ON</sub> = GND, V <sub>OUT</sub> = 0 V	V <sub>IN</sub> = 5.0 V	−40°C to 105°C	0.2	8	μA	
				−40°C to 125°C		36		
			V <sub>IN</sub> = 3.3 V	−40°C to 105°C	0.02	3		
				−40°C to 125°C		13		
			V <sub>IN</sub> = 1.8 V	−40°C to 105°C	0.01	2		
				−40°C to 125°C		6		
			V <sub>IN</sub> = 0.8 V	−40°C to 105°C	0.005	1		
				−40°C to 125°C		4		
I <sub>ON</sub>	ON pin input leakage current	V <sub>ON</sub> = 5.5 V		−40°C to 105°C		0.5	μA	
				−40°C to 125°C		0.5		
RESISTANCE CHARACTERISTICS								
R <sub>ON</sub>	ON-state resistance	I <sub>OUT</sub> = −200 mA, V <sub>BIAS</sub> = 5.0 V	V <sub>IN</sub> = 5.0 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
			V <sub>IN</sub> = 3.3 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
			V <sub>IN</sub> = 1.8 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
			V <sub>IN</sub> = 1.5 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
			V <sub>IN</sub> = 1.2 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
			V <sub>IN</sub> = 0.8 V	25°C	16	23	mΩ	
				−40°C to 105°C		25		
				−40°C to 125°C		26		
R <sub>PD</sub> <sup>(1)</sup>	Output pull-down resistance	V <sub>IN</sub> = 5.0 V, V <sub>ON</sub> = 0 V, I <sub>OUT</sub> = 1 mA		−40°C to 105°C	225	300	Ω	
				−40°C to 125°C	225	300		

(1) TPS22965-Q1 and TPS22965W-Q1 Only

## 8.6 Electrical Characteristics

Unless otherwise noted, the specification in the following table applies over the operating ambient temperature  $-40^{\circ}\text{C} \leq T_A \leq 105^{\circ}\text{C}$  (TPS22965N-Q1, TPS22965-Q1),  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$  (TPS22965W-Q1) and  $V_{\text{BIAS}} = 2.5\text{ V}$ . Typical values are for  $T_A = 25^{\circ}\text{C}$ .

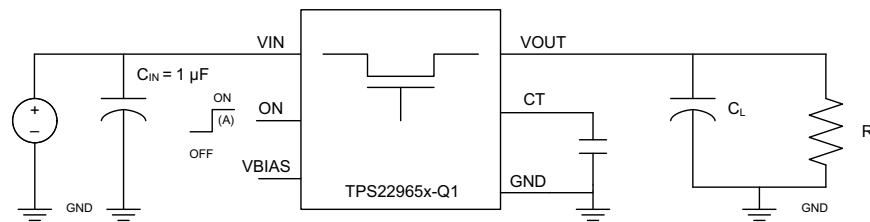
PARAMETER		TEST CONDITIONS		T <sub>A</sub>	MIN	TYP	MAX	UNIT
POWER SUPPLIES AND CURRENTS								
I <sub>Q</sub> V <sub>BIAS</sub>	V <sub>BIAS</sub> quiescent current	I <sub>OUT</sub> = 0 mA, V <sub>IN</sub> = V <sub>ON</sub> = V <sub>BIAS</sub> = 2.5 V		−40°C to 105°C		20	30	μA
				−40°C to 125°C		20	30	
I <sub>SD</sub> V <sub>BIAS</sub>	V <sub>BIAS</sub> shutdown current	V <sub>ON</sub> = GND, V <sub>OUT</sub> = 0 V		−40°C to 105°C			2	μA
				−40°C to 125°C			2	
I <sub>SD</sub> V <sub>IN</sub>	V <sub>IN</sub> off-state supply current	V <sub>ON</sub> = GND, V <sub>OUT</sub> = 0 V	V <sub>IN</sub> = 2.5 V	−40°C to 105°C		0.01	3	μA
				−40°C to 125°C			13	
			V <sub>IN</sub> = 1.8 V	−40°C to 105°C		0.01	2	
				−40°C to 125°C			6	
			V <sub>IN</sub> = 1.2 V	−40°C to 105°C		0.005	2	
				−40°C to 125°C			6	
			V <sub>IN</sub> = 0.8 V	−40°C to 105°C		0.003	1	
				−40°C to 125°C			4	
I <sub>ON</sub>	ON pin input leakage current	V <sub>ON</sub> = 5.5 V		−40°C to 105°C			0.5	μA
				−40°C to 125°C			0.5	
RESISTANCE CHARACTERISTICS								
R <sub>ON</sub>	ON-state resistance	I <sub>OUT</sub> = −200 mA, V <sub>BIAS</sub> = 2.5 V	V <sub>IN</sub> = 2.5 V	25°C		20	26	mΩ
				−40°C to 105°C			28	
				−40°C to 125°C			29	
			V <sub>IN</sub> = 1.8 V	25°C		19	26	mΩ
				−40°C to 105°C			28	
				−40°C to 125°C			29	
			V <sub>IN</sub> = 1.5 V	25°C		18	25	mΩ
				−40°C to 105°C			27	
				−40°C to 125°C			28	
			V <sub>IN</sub> = 1.2 V	25°C		18	25	mΩ
				−40°C to 105°C			27	
				−40°C to 125°C			28	
V <sub>IN</sub> = 0.8 V	25°C		17	25	mΩ			
	−40°C to 105°C			27				
	−40°C to 125°C			28				
R <sub>PD</sub> <sup>(1)</sup>	Output pull-down resistance	V <sub>IN</sub> = 2.5 V, V <sub>ON</sub> = 0 V, I <sub>OUT</sub> = 1 mA		−40°C to 105°C		275	325	Ω
				−40°C to 125°C		275	330	

(1) TPS22965-Q1 and TPS22965W-Q1 only

## 8.7 Switching Characteristics

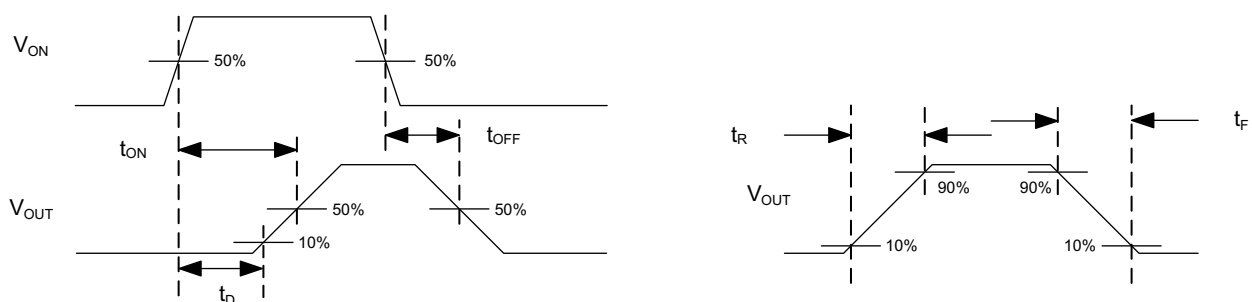
Over operating free-air temperature range (unless otherwise noted). Switching characteristics shown below are only valid for the power-up sequence where VIN and VBIAS are already in steady state condition before the ON pin is asserted high.

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
V <sub>IN</sub> = V <sub>ON</sub> = V <sub>BIAS</sub> = 5 V, T <sub>A</sub> = 25°C (unless otherwise noted)						
t <sub>ON</sub>	Turn-on time	R <sub>L</sub> = 10 Ω, C <sub>L</sub> = 0.1 μF, C <sub>T</sub> = 1000 pF, C <sub>IN</sub> = 1 μF		1600		μs
t <sub>OFF</sub>	Turn-off time			9		
t <sub>R</sub>	V <sub>OUT</sub> rise time			1985		
t <sub>F</sub>	V <sub>OUT</sub> fall time			3		
t <sub>D</sub>	ON delay time			660		
V <sub>IN</sub> = 0.8 V, V <sub>ON</sub> = V <sub>BIAS</sub> = 5 V, T <sub>A</sub> = 25°C (unless otherwise noted)						
t <sub>ON</sub>	Turn-on time	R <sub>L</sub> = 10 Ω, C <sub>L</sub> = 0.1 μF, C <sub>T</sub> = 1000 pF, C <sub>IN</sub> = 1 μF		730		μs
t <sub>OFF</sub>	Turn-off time			100		
t <sub>R</sub>	V <sub>OUT</sub> rise time			380		
t <sub>F</sub>	V <sub>OUT</sub> fall time			8		
t <sub>D</sub>	ON delay time			560		
V <sub>IN</sub> = 2.5 V, V <sub>ON</sub> = 5 V, V <sub>BIAS</sub> = 2.5 V, T <sub>A</sub> = 25°C (unless otherwise noted)						
t <sub>ON</sub>	Turn-on time	R <sub>L</sub> = 10 Ω, C <sub>L</sub> = 0.1 μF, C <sub>T</sub> = 1000 pF, C <sub>IN</sub> = 1 μF		2435		μs
t <sub>OFF</sub>	Turn-off time			9		
t <sub>R</sub>	V <sub>OUT</sub> rise time			2515		
t <sub>F</sub>	V <sub>OUT</sub> fall time			4		
t <sub>D</sub>	ON delay time			1230		
V <sub>IN</sub> = 0.8 V, V <sub>ON</sub> = 5 V, V <sub>BIAS</sub> = 2.5 V, T <sub>A</sub> = 25°C (unless otherwise noted)						
t <sub>ON</sub>	Turn-on time	R <sub>L</sub> = 10 Ω, C <sub>L</sub> = 0.1 μF, C <sub>T</sub> = 1000 pF, C <sub>IN</sub> = 1 μF		1565		μs
t <sub>OFF</sub>	Turn-off time			70		
t <sub>R</sub>	V <sub>OUT</sub> rise time			930		
t <sub>F</sub>	V <sub>OUT</sub> fall time			8		
t <sub>D</sub>	ON delay time			1110		



A. Rise and fall times of the control signal is 100 ns.

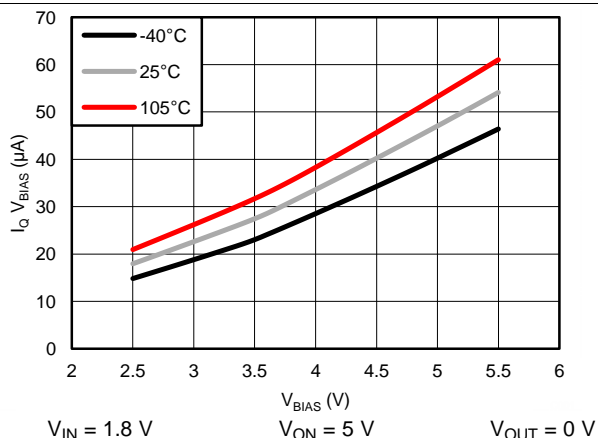
**Figure 1. Test Circuit**



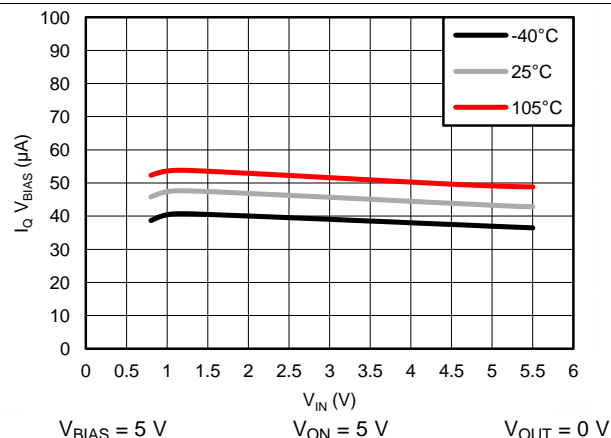
**Figure 2. t<sub>ON</sub>/t<sub>OFF</sub> Waveforms**



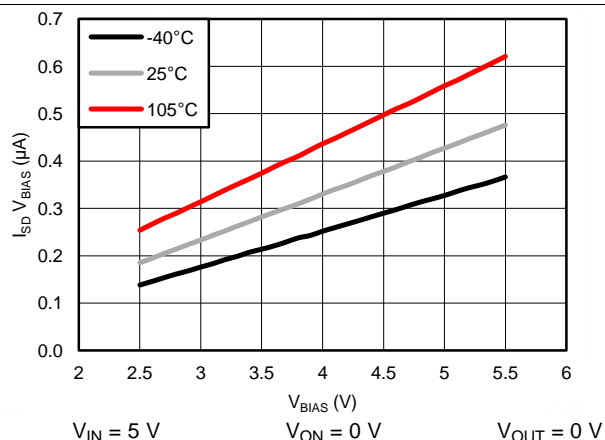
## 8.8 Typical DC Characteristics



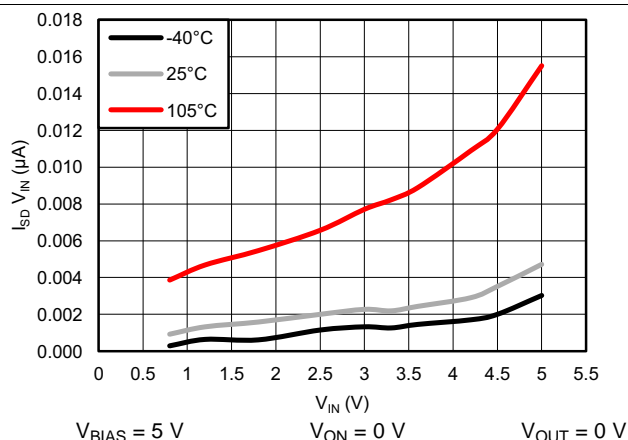
**Figure 3.  $V_{BIAS}$  Quiescent Current vs.  $V_{BIAS}$**



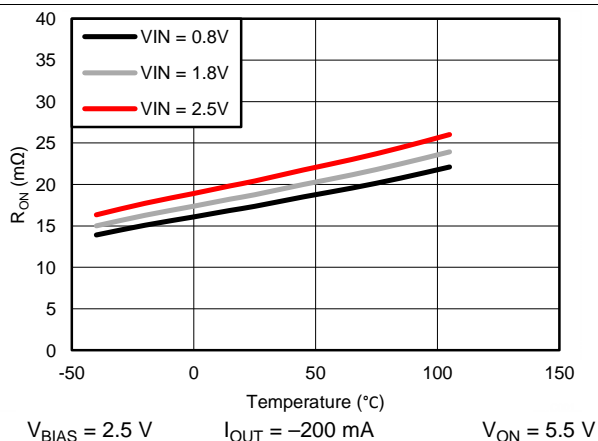
**Figure 4.  $I_Q V_{BIAS}$  vs  $V_{IN}$**



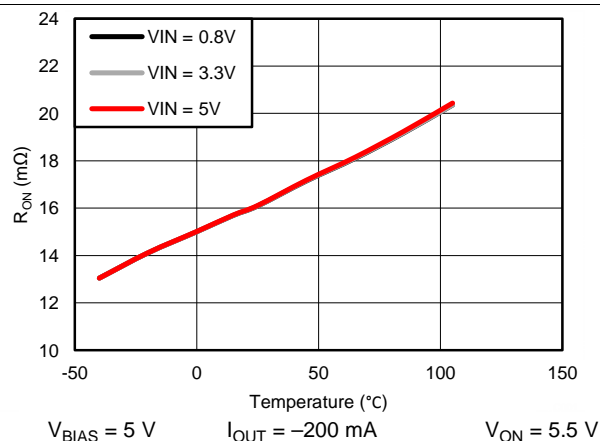
**Figure 5.  $I_{SD} V_{BIAS}$  vs  $V_{BIAS}$**



**Figure 6.  $I_{SD} V_{IN}$  vs  $V_{IN}$**



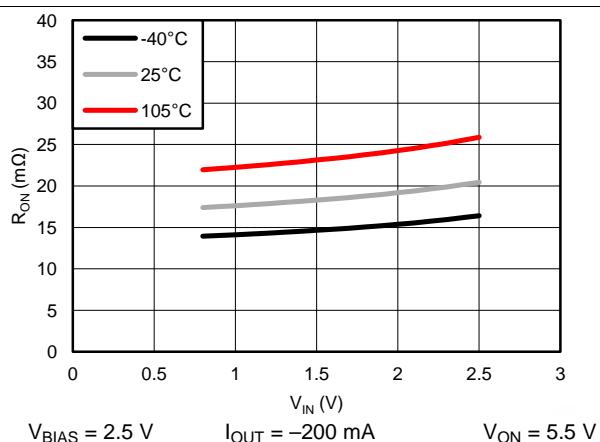
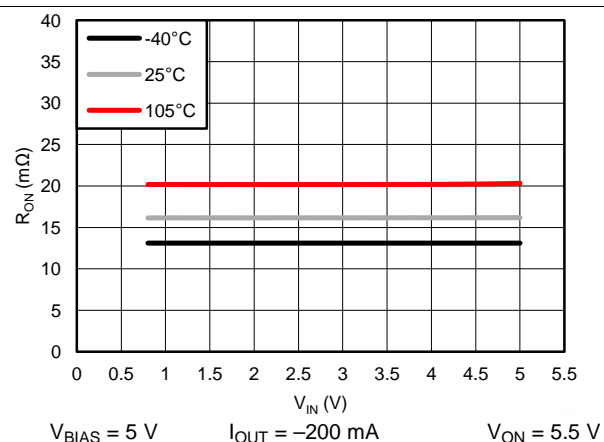
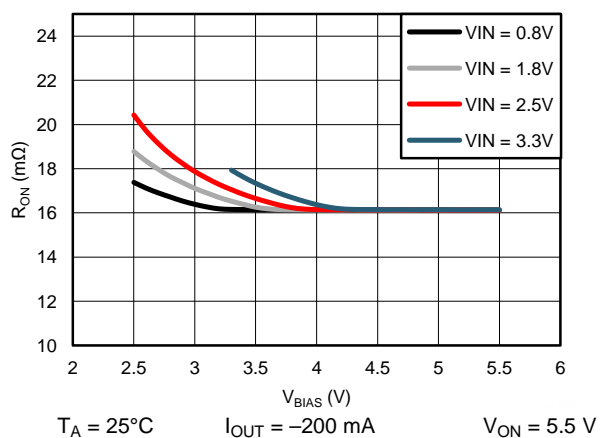
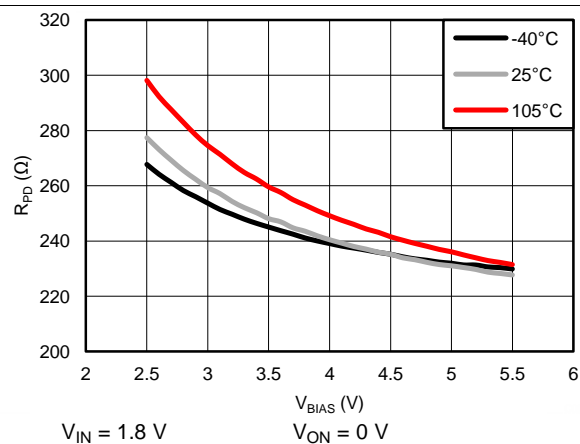
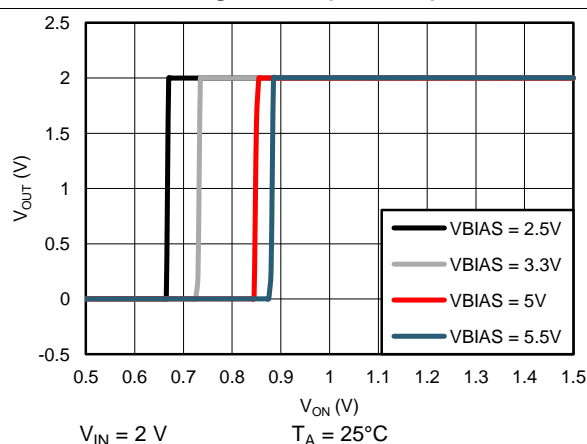
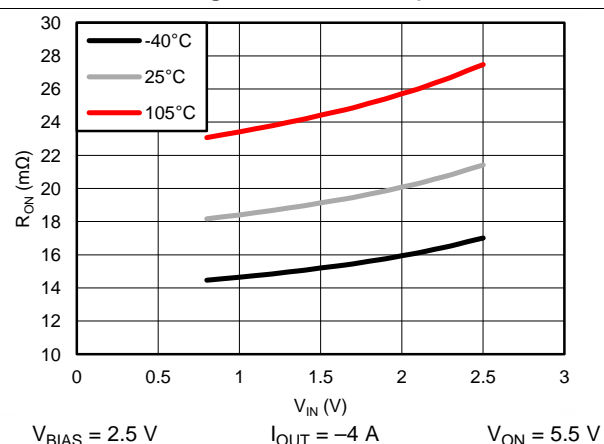
**Figure 7.  $R_{ON}$  vs Ambient Temperature**



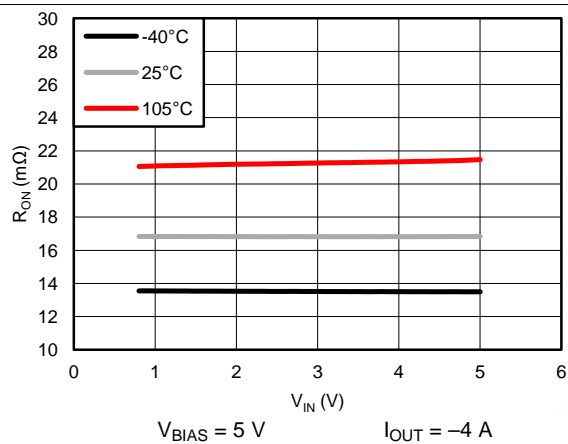
**Note:** All three  $R_{ON}$  curves have the same values; therefore, only one line is visible.

**Figure 8.  $R_{ON}$  vs Ambient Temperature**

## Typical DC Characteristics (continued)

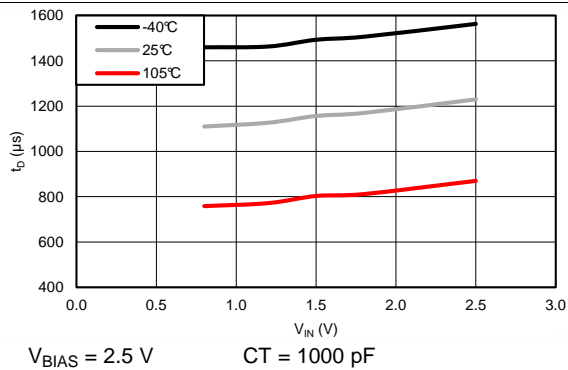
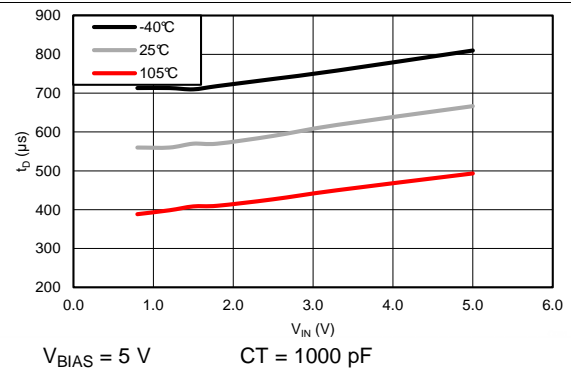
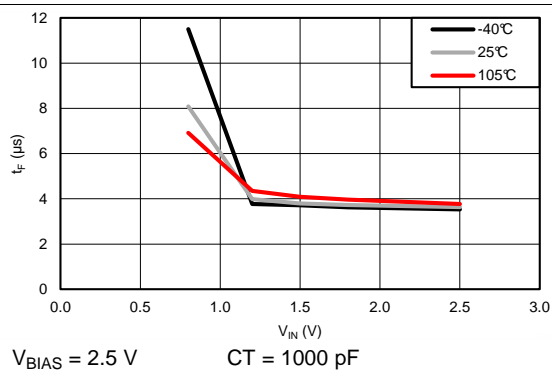
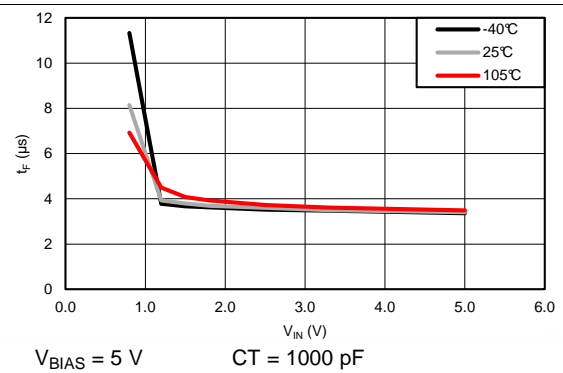
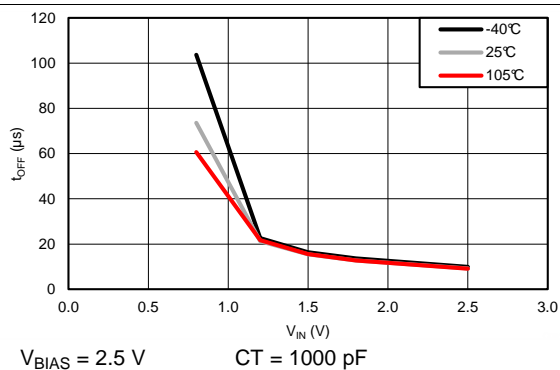
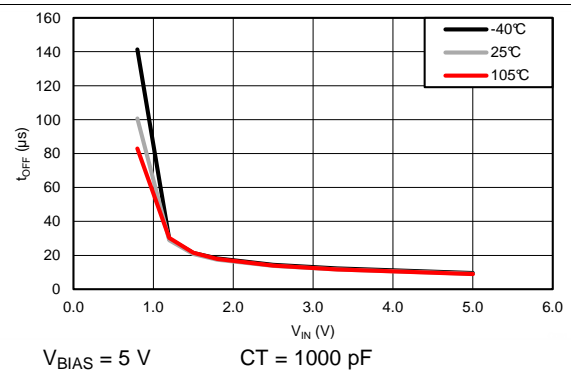

**Figure 9.  $R_{ON}$  vs  $V_{IN}$** 

**Figure 10.  $R_{ON}$  vs  $V_{IN}$** 

**Figure 11.  $R_{ON}$  vs  $V_{BIAS}$** 

**Figure 12.  $R_{PD}$  vs  $V_{BIAS}$** 

**Figure 13.  $V_{OUT}$  vs  $V_{ON}$** 

**Figure 14.  $R_{ON}$  vs  $V_{IN}$**

## Typical DC Characteristics (continued)



**Figure 15.  $R_{ON}$  vs  $V_{IN}$**

## 8.9 Typical Switching Characteristics

 $T_A = 25^\circ\text{C}$ ,  $C_T = 1000\text{ pF}$ ,  $C_{IN} = 1\text{ }\mu\text{F}$ ,  $C_L = 0.1\text{ }\mu\text{F}$ ,  $R_L = 10\text{ }\Omega$ 

**Figure 16.  $t_D$  vs  $V_{IN}$** 

**Figure 17.  $t_D$  vs  $V_{IN}$** 

**Figure 18.  $t_F$  vs  $V_{IN}$** 

**Figure 19.  $t_F$  vs  $V_{IN}$** 

**Figure 20.  $t_{OFF}$  vs  $V_{IN}$** 

**Figure 21.  $t_{OFF}$  vs  $V_{IN}$**

## Typical Switching Characteristics (continued)

$T_A = 25^\circ\text{C}$ ,  $C_T = 1000\text{ pF}$ ,  $C_{IN} = 1\text{ }\mu\text{F}$ ,  $C_L = 0.1\text{ }\mu\text{F}$ ,  $R_L = 10\text{ }\Omega$

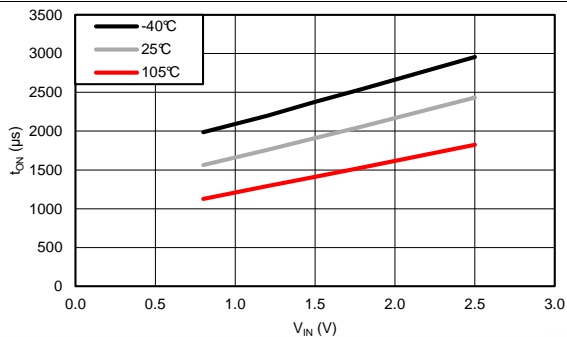


Figure 22.  $t_{ON}$  vs  $V_{IN}$

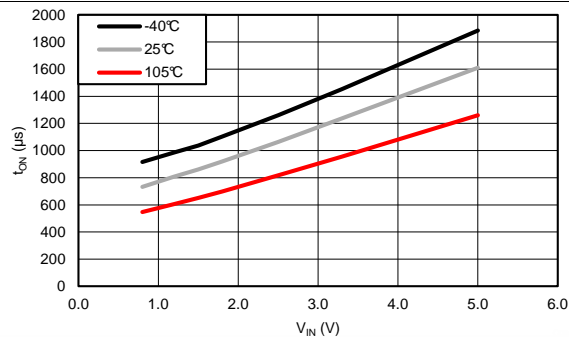


Figure 23.  $t_{ON}$  vs  $V_{IN}$

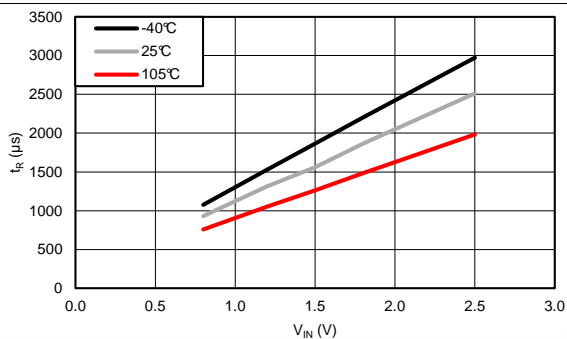


Figure 24.  $t_R$  vs  $V_{IN}$

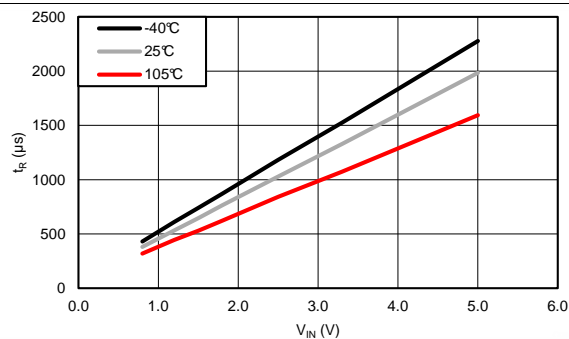


Figure 25.  $t_R$  vs  $V_{IN}$

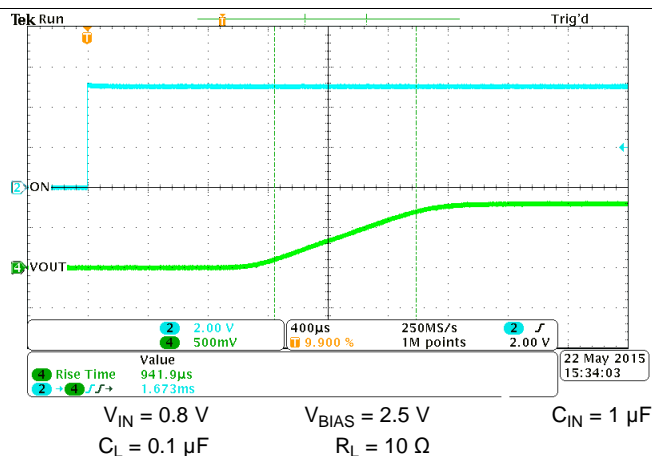


Figure 26. Turn-on Response Time

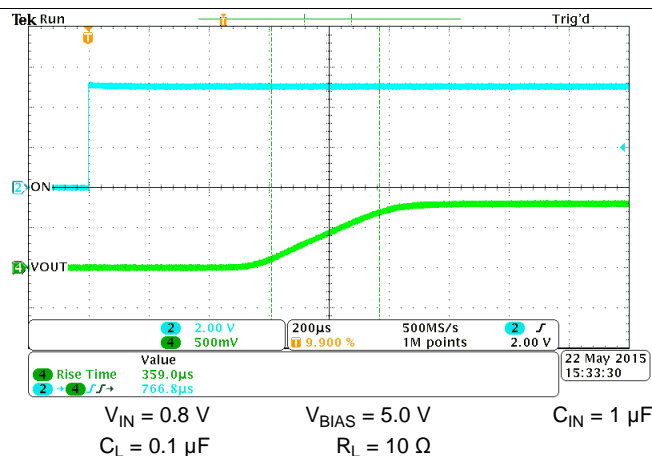
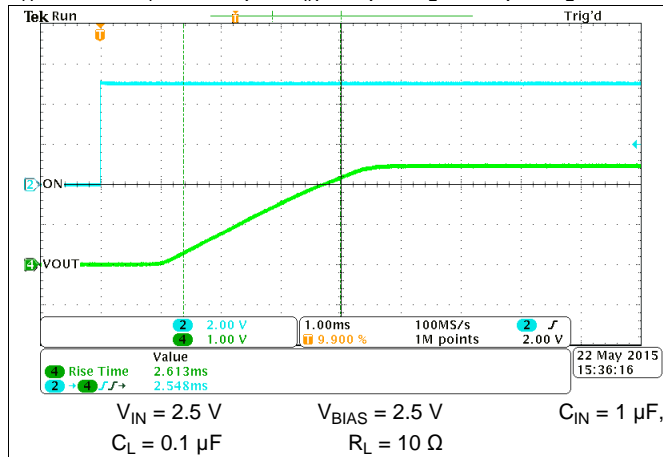
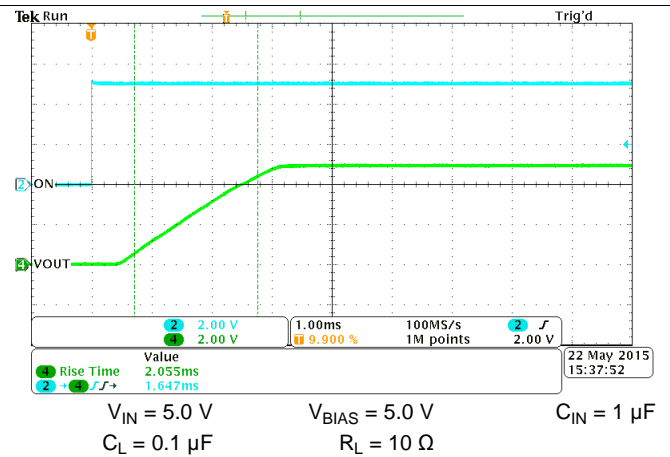
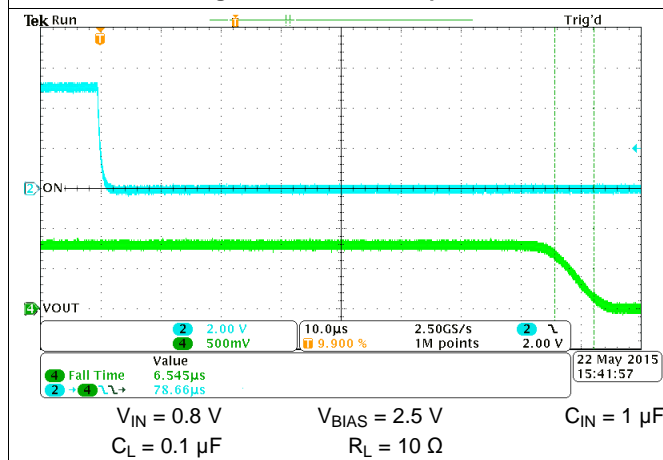
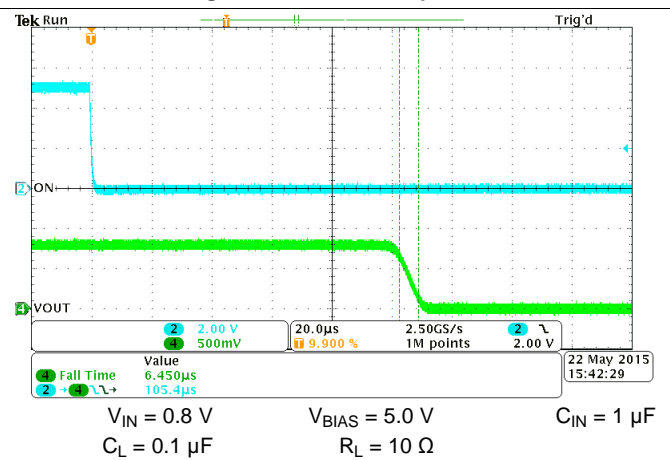
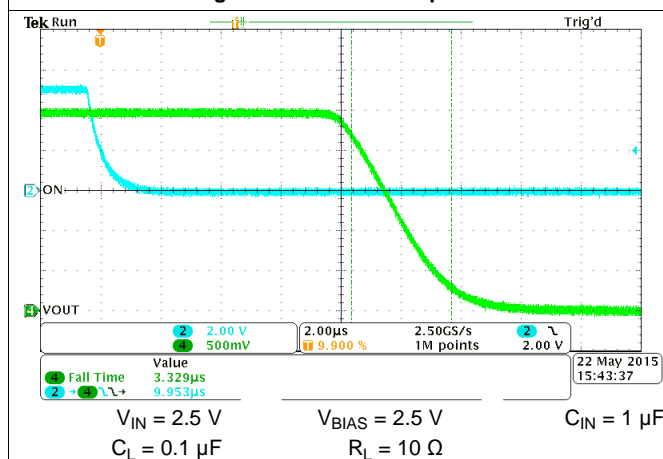
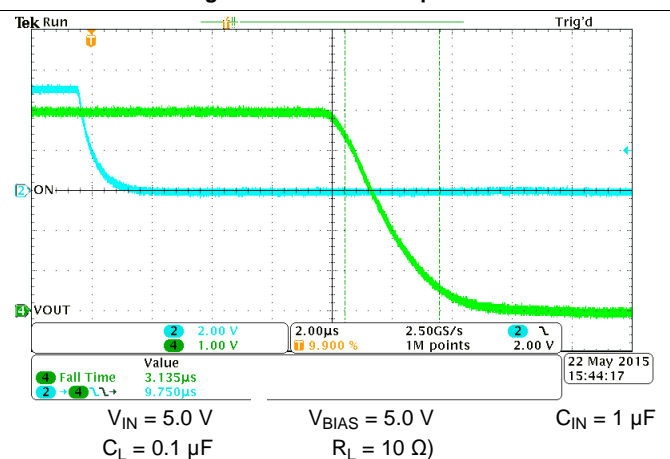


Figure 27. Turn-on Response Time

## Typical Switching Characteristics (continued)

 $T_A = 25^\circ\text{C}$ ,  $C_T = 1000\text{ pF}$ ,  $C_{IN} = 1\text{ }\mu\text{F}$ ,  $C_L = 0.1\text{ }\mu\text{F}$ ,  $R_L = 10\text{ }\Omega$ 

**Figure 28. Turn-on Response Time**

**Figure 29. Turn-on Response Time**

**Figure 30. Turn-off Response Time**

**Figure 31. Turn-off Response Time**

**Figure 32. Turn-off Response Time**

**Figure 33. Turn-off Response Time**

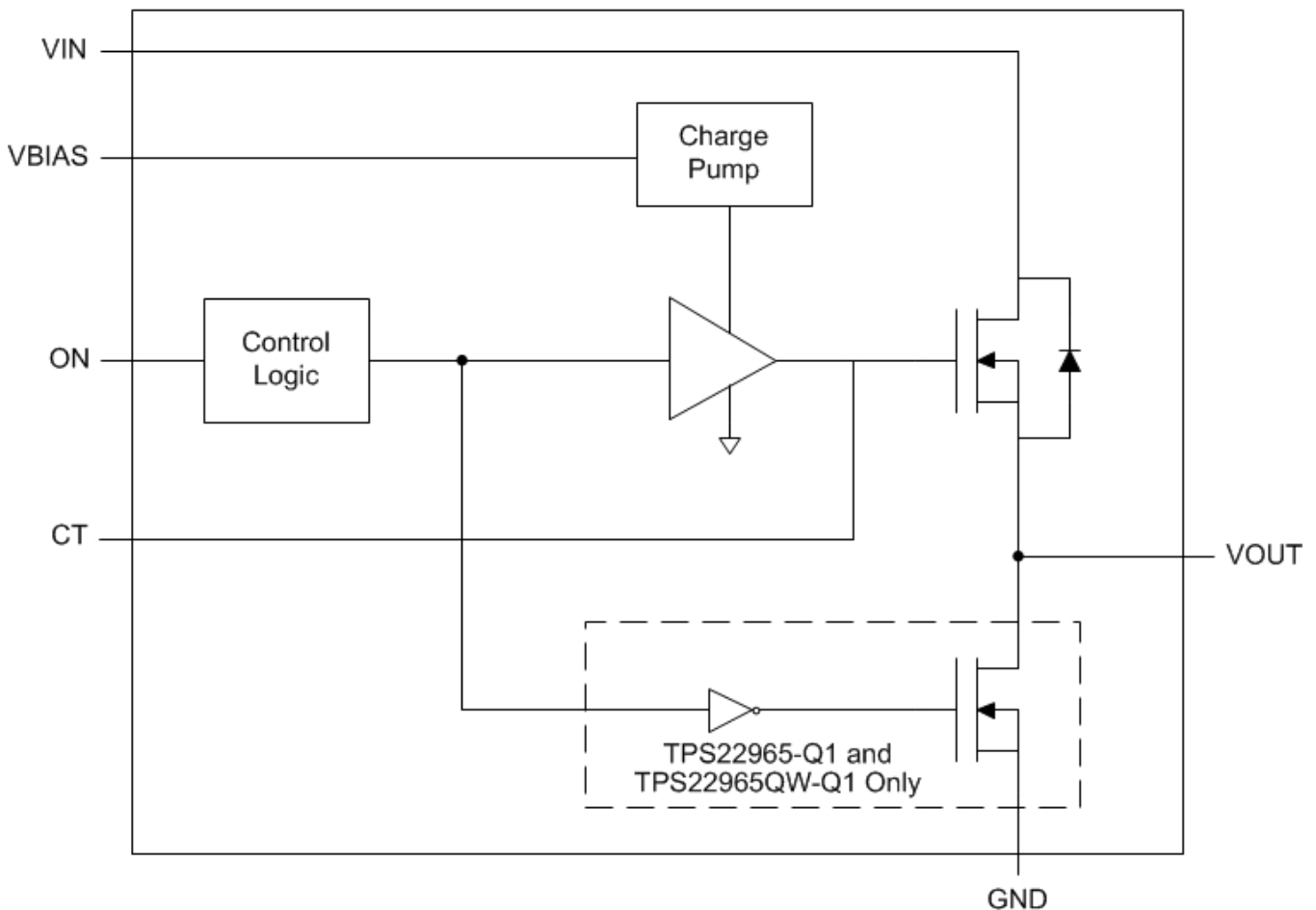
## 9 Detailed Description

### 9.1 Overview

The TPS22965x-Q1 is a single channel, 4-A load switch in an 8-pin SON package. To reduce the voltage drop in high current rails, the device implements an ultra-low resistance N-channel MOSFET. The device has a programmable slew rate for applications that require specific rise-time.

The device has very low leakage current during off state. This prevents downstream circuits from pulling high standby current from the supply. Integrated control logic, driver, power supply, and output discharge FET eliminates the need for any external components, which reduces solution size and BOM count.

### 9.2 Functional Block Diagram



## 9.3 Feature Description

### 9.3.1 Adjustable Rise Time

A capacitor to GND on the CT pin sets the slew rate. The voltage on the CT pin can be as high as 12 V. Therefore, the minimum voltage rating for the CT cap should be 25 V for optimal performance. An approximate formula for the relationship between CT and slew rate when  $V_{BIAS}$  is set to 5 V is shown in Equation 1 below. This equation accounts for 10% to 90% measurement on  $V_{OUT}$  and does **NOT** apply for CT = 0 pF. Use Table 1 to determine rise times for when CT = 0 pF.

$$SR = 0.38 \times CT + 34 \quad (1)$$

Where,

SR = slew rate (in  $\mu\text{s/V}$ )

CT = the capacitance value on the CT pin (in pF)

The units for the constant 34 are  $\mu\text{s/V}$ . The units for the constant 0.38 are  $\mu\text{s}/(\text{V} \cdot \text{pF})$ .

Rise time can be calculated by multiplying the input voltage by the slew rate. The table below contains rise time values measured on a typical device. Rise times shown below are only valid for the power-up sequence where  $V_{IN}$  and  $V_{BIAS}$  are already in steady state condition before the ON pin is asserted high.

**Table 1. Rise Time vs CT Capacitor**

CT (pF)	RISE TIME ( $\mu\text{s}$ ) 10% - 90%, $C_L = 0.1 \mu\text{F}$ , $C_{IN} = 1 \mu\text{F}$ , $R_L = 10 \Omega$ , $V_{BIAS} = 5 \text{ V}$ TYPICAL VALUES at 25°C with a 25V X7R 10% CERAMIC CAPACITOR on CT						
	$V_{IN} = 5 \text{ V}$	$V_{IN} = 3.3 \text{ V}$	$V_{IN} = 1.8 \text{ V}$	$V_{IN} = 1.5 \text{ V}$	$V_{IN} = 1.2 \text{ V}$	$V_{IN} = 1.05 \text{ V}$	$V_{IN} = 0.8 \text{ V}$
0	180	136	94	84	74	70	60
220	547	378	232	202	173	157	129
470	962	654	386	333	282	252	206
1000	1983	1330	765	647	533	476	382
2200	4013	2693	1537	1310	1077	959	766
4700	8207	5490	3137	2693	2200	1970	1590
10000	17700	11767	6697	5683	4657	4151	3350

### 9.3.2 Quick Output Discharge (TPS22965-Q1 and TPS22965W-Q1 Only)

The TPS22965-Q1 and TPS22965W-Q1 include a Quick Output Discharge (QOD) feature. When the switch is disabled, a discharge resistor is connected between VOUT and GND. This resistor has a typical value of 225  $\Omega$  and prevents the output from floating while the switch is disabled.

### 9.3.3 Low Power Consumption During Off State

The  $I_{SD}$   $V_{IN}$  supply current is 0.01  $\mu\text{A}$  typical at 1.8 V<sub>IN</sub>. Typically, the downstream loads would have a significantly higher off-state leakage current. The load switch allows system standby power consumption to be reduced.

## 9.4 Device Functional Modes

The Table 2, below, lists the VOUT pin state as determined by the ON pin.

**Table 2. Functional Table**

ON	TPS22965N-Q1	TPS22965-Q1 and TPS22965W-Q1
L	Open	GND
H	VIN	VIN



## 10 Applications and Implementation

### 10.1 Application Information

This section will highlight some of the design considerations when implementing this device in various applications. A PSPIICE model for this device is also available in the product page of this device on [www.ti.com](http://www.ti.com) for further aid.

#### 10.1.1 VIN to VOUT Voltage Drop

The VIN to VOUT voltage drop in the device is determined by the  $R_{ON}$  of the device and the load current. The  $R_{ON}$  of the device depends upon the  $V_{IN}$  and  $V_{BIAS}$  conditions of the device. Refer to the  $R_{ON}$  specification of the device in the [Electrical Characteristics](#) table of this datasheet. Once the  $R_{ON}$  of the device is determined based upon the  $V_{IN}$  and  $V_{BIAS}$  conditions, use [Equation 2](#) to calculate the VIN to VOUT voltage drop:

$$\Delta V = I_{LOAD} \times R_{ON} \quad (2)$$

where

- $\Delta V$  = voltage drop from VIN to VOUT
- $I_{LOAD}$  = load current
- $R_{ON}$  = On-resistance of the device for a specific  $V_{IN}$  and  $V_{BIAS}$  combination

An appropriate  $I_{LOAD}$  must be chosen such that the  $I_{MAX}$  specification of the device is not violated.

#### 10.1.2 On/Off Control

The ON pin controls the state of the switch. ON is active high and has a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic thresholds. It can be used with any microcontroller with 1.2 V or higher GPIO voltage. This pin cannot be left floating and must be driven either high or low for proper functionality.

#### 10.1.3 Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor or short-circuit, a capacitor needs to be placed between VIN and GND. A 1- $\mu$ F ceramic capacitor,  $C_{IN}$ , placed close to the pins, is usually sufficient. Higher values of  $C_{IN}$  can be used to further reduce the voltage drop during high current applications. When switching heavy loads, it is recommended to have an input capacitor about 10 times higher than the output capacitor to avoid excessive voltage drop.

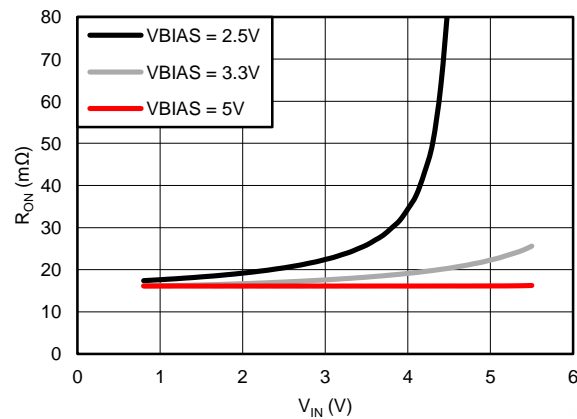
#### 10.1.4 Output Capacitor (Optional)

Due to the integrated body diode in the NMOS switch, a  $C_{IN}$  greater than  $C_L$  is highly recommended. A  $C_L$  greater than  $C_{IN}$  can cause  $V_{OUT}$  to exceed  $V_{IN}$  when the system supply is removed. This could result in current flow through the body diode from  $V_{OUT}$  to  $V_{IN}$ . A  $C_{IN}$  to  $C_L$  ratio of 10 to 1 is recommended for minimizing  $V_{IN}$  dip caused by inrush currents during startup; however, a 10 to 1 ratio for capacitance is not required for proper functionality of the device. A ratio smaller than 10 to 1 (such as 1 to 1) could cause slightly more  $V_{IN}$  dip upon turn-on due to inrush currents. This can be mitigated by increasing the capacitance on the CT pin for a longer rise time (see the [Adjustable Rise Time](#) section).

#### 10.1.5 VIN and VBIAS Voltage Range

For optimal  $R_{ON}$  performance, make sure  $V_{IN} \leq V_{BIAS}$ . The device will still be functional if  $V_{IN} > V_{BIAS}$  but it will exhibit  $R_{ON}$  greater than what is listed in the [Electrical Characteristics](#) table. See [Figure 34](#) for an example of a typical device. Notice the increasing  $R_{ON}$  as  $V_{IN}$  exceeds  $V_{BIAS}$  voltage. Be sure to never exceed the maximum voltage rating for  $V_{IN}$  and  $V_{BIAS}$ .

## Application Information (continued)

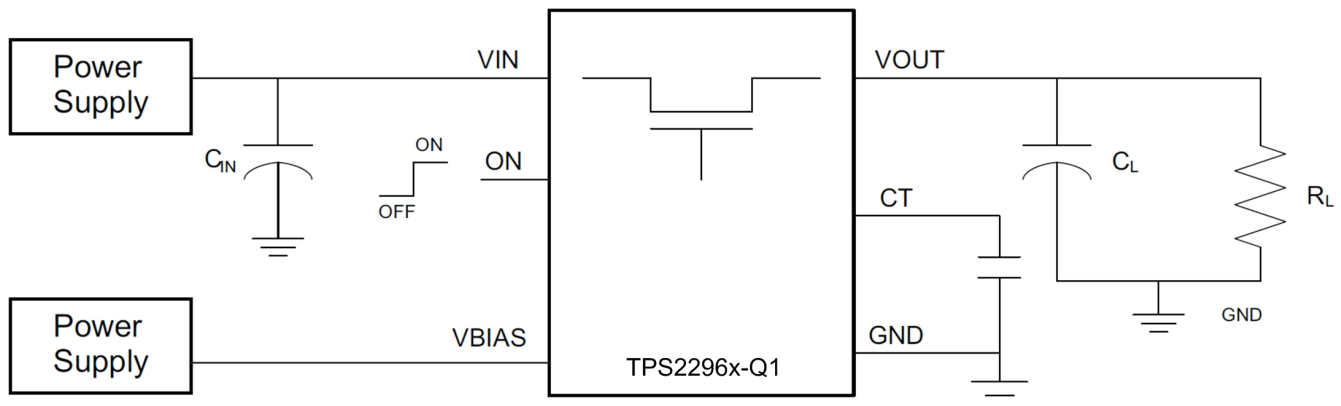


$$I_{OUT} = -200\text{mA} \quad T_A = 25^\circ\text{C}$$

**Figure 34. R<sub>ON</sub> vs. V<sub>IN</sub> (V<sub>IN</sub> > V<sub>BIAS</sub>)**

## 10.2 Typical Application

This application demonstrates how the TPS22965x-Q1 can be used to power downstream modules.



**Figure 35. Schematic for Powering a Downstream Module**

### 10.2.1 Design Requirements

DESIGN PARAMETER	EXAMPLE VALUE
V <sub>IN</sub>	3.3 V
V <sub>BIAS</sub>	5 V
C <sub>L</sub>	22 μF
Maximum Acceptable Inrush Current	400 mA

## 10.2.2 Detailed Design Procedure

### 10.2.2.1 Inrush Current

When the switch is enabled, the output capacitors must be charged up from 0-V to the set value (3.3-V in this example). This charge arrives in the form of inrush current. Inrush current can be calculated using the following equation:

$$\text{Inrush Current} = C \times dV/dt \quad (3)$$

Where:

C = output capacitance

dV = output voltage

dt = rise time

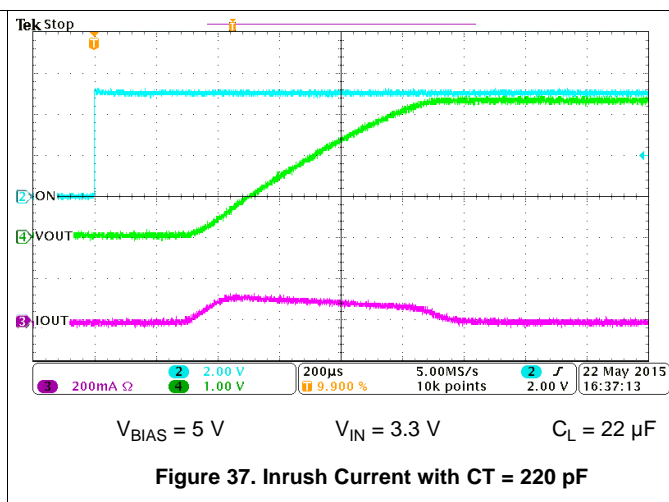
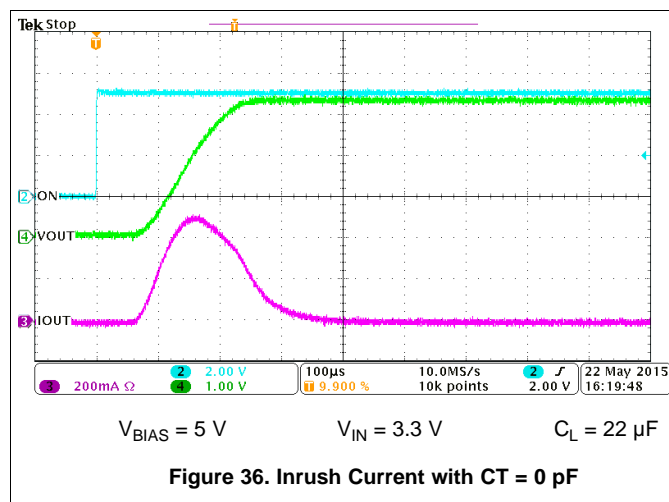
The TPS22965x-Q1 offers adjustable rise time for VOUT. This feature allows the user to control the inrush current during turn-on. The appropriate rise time can be calculated using the design requirements and the inrush current equation.

$$400 \text{ mA} = 22 \text{ } \mu\text{F} \times 3.3 \text{ V} / dt \quad (4)$$

$$dt = 181.5 \text{ } \mu\text{s} \quad (5)$$

To ensure an inrush current of less than 400 mA, choose a CT value that will yield a rise time of more than 181.5μs. See the oscilloscope captures below ([Application Curves](#)) for an example of how the CT capacitor can be used to reduce inrush current.

## 10.2.3 Application Curves



## 11 Power Supply Recommendations

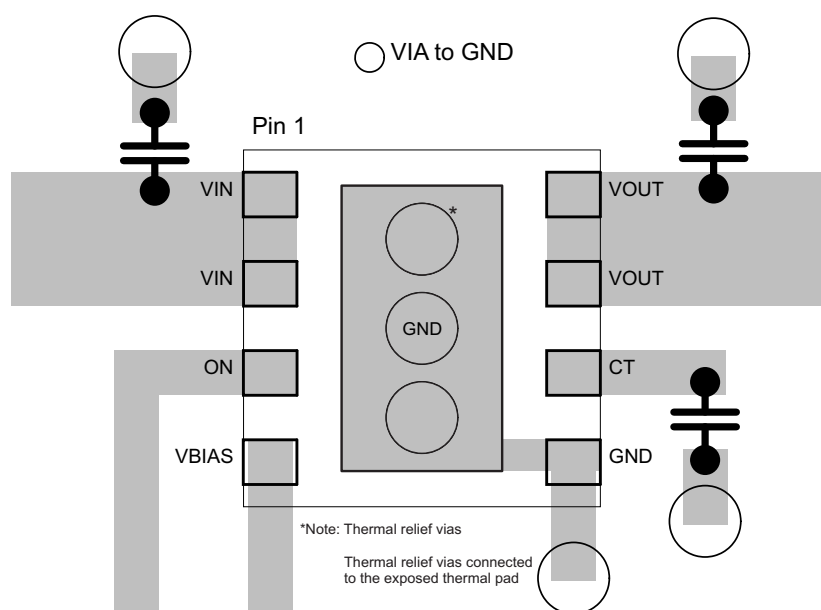
The device is designed to operate from a VBIAS range of 2.5 V to 5.5 V and a VIN range of 0.8 V to VBIAS.

## 12 Layout

### 12.1 Board Layout and Thermal Considerations

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance. The CT trace should be as short as possible to avoid parasitic capacitance.

### 12.2 Layout Example



**Figure 38. Layout Recommendation**

### 12.3 Thermal Consideration

The maximum IC junction temperature should be restricted to 150°C under normal operating conditions. To calculate the maximum allowable dissipation,  $P_{D(max)}$  for a given output current and ambient temperature, use the following equation as a guideline:

$$P_{D(max)} = \frac{T_{J(max)} - T_A}{\theta_{JA}}$$

where

- $P_{D(max)}$  = maximum allowable power dissipation
- $T_{J(max)}$  = maximum allowable junction temperature (150°C for the TPS22965x-Q1)
- $T_A$  = ambient temperature of the device
- $\theta_{JA}$  = junction to air thermal impedance. See the [Thermal Information](#) table. This parameter is highly dependent upon board layout

(6)

Refer to [Figure 38](#), notice the thermal vias located under the exposed thermal pad of the device. This allows for thermal diffusion away from the device.

## 13 Device and Documentation Support

### 13.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 13.2 Trademarks

E2E is a trademark of Texas Instruments.  
All other trademarks are the property of their respective owners.

### 13.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 13.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22965NTDSGRQ1	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	ZDXI	<a href="#">Samples</a>
TPS22965NTDSGTQ1	PREVIEW	WSON	DSG	8	250	TBD	Call TI	Call TI	-40 to 105		
TPS22965QWDSGRQ1	PREVIEW	WSON	DSG	8	3000	TBD	Call TI	Call TI	-40 to 125	11A	
TPS22965TDSGRQ1	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	ZYE	<a href="#">Samples</a>
TPS22965TDSGTQ1	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	ZYE	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF TPS22965-Q1 :**

- Catalog: [TPS22965](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22965NTDSGRQ1	WSO	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS22965TDSGRQ1	WSO	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS22965TDSGTQ1	WSO	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2



## TAPE AND REEL BOX DIMENSIONS

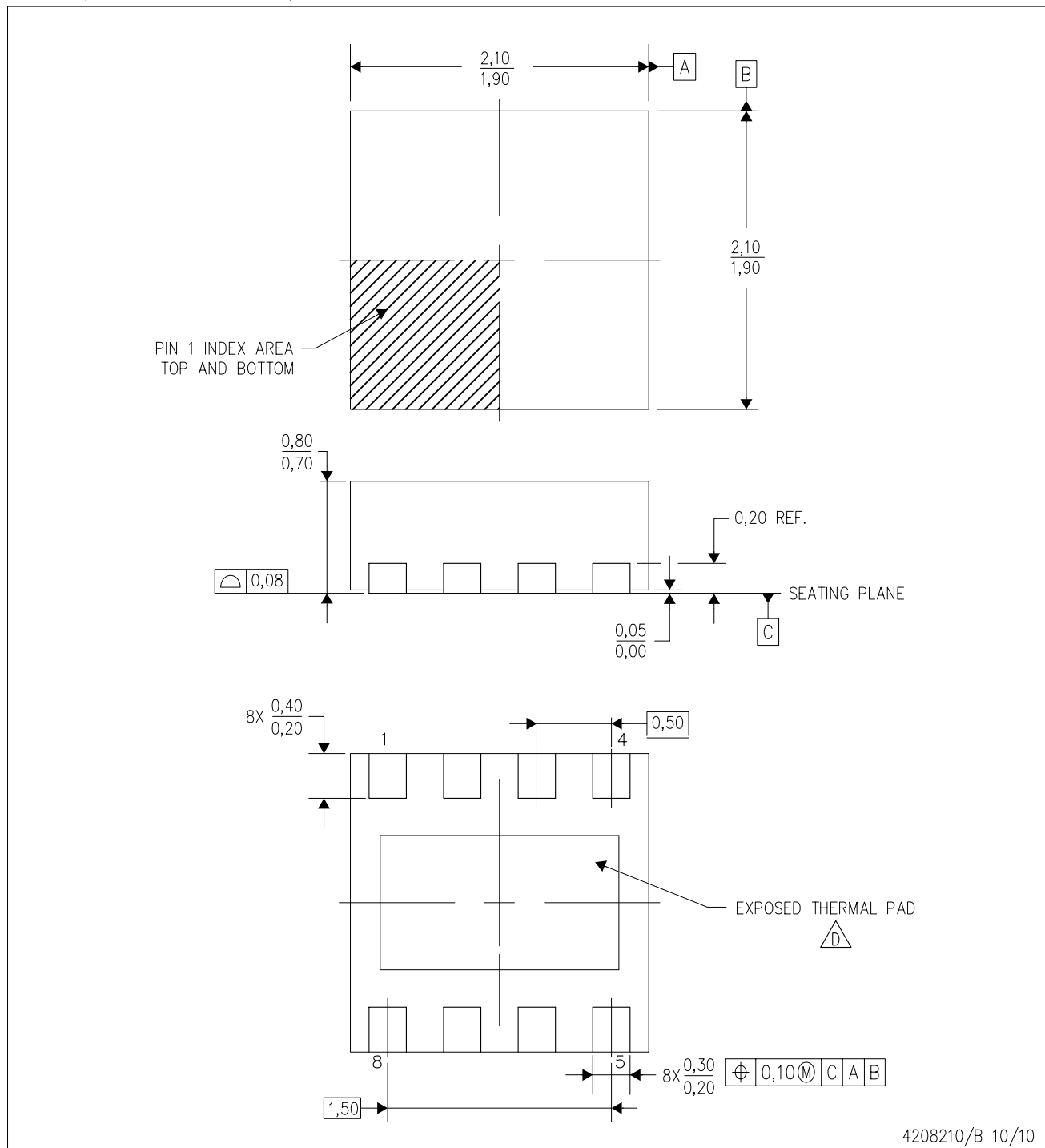


\*All dimensions are nominal


Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22965NTDSGRQ1	WSON	DSG	8	3000	210.0	185.0	35.0
TPS22965TDSGRQ1	WSON	DSG	8	3000	210.0	185.0	35.0
TPS22965TDSGTQ1	WSON	DSG	8	250	210.0	185.0	35.0

DSG (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



4208210/B 10/10

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-Leads (QFN) package configuration.
  -  The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
  - E. Falls within JEDEC MO-229.

## THERMAL PAD MECHANICAL DATA

DSG (S-PWSON-N8)

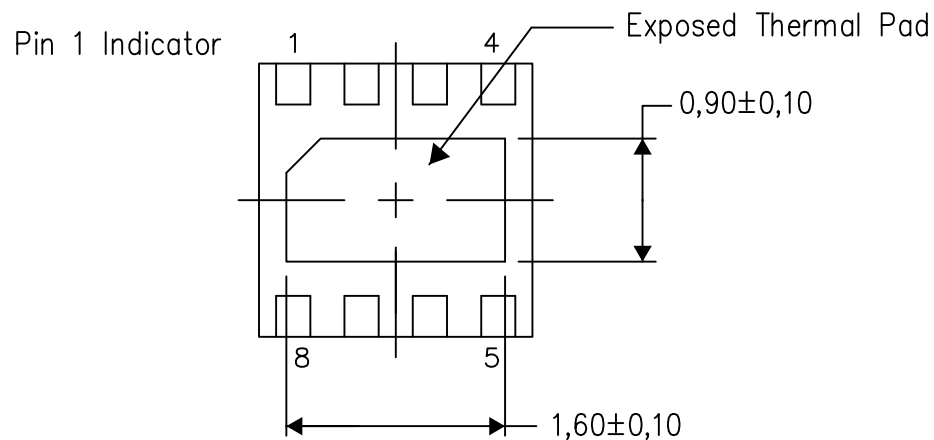
PLASTIC SMALL OUTLINE NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

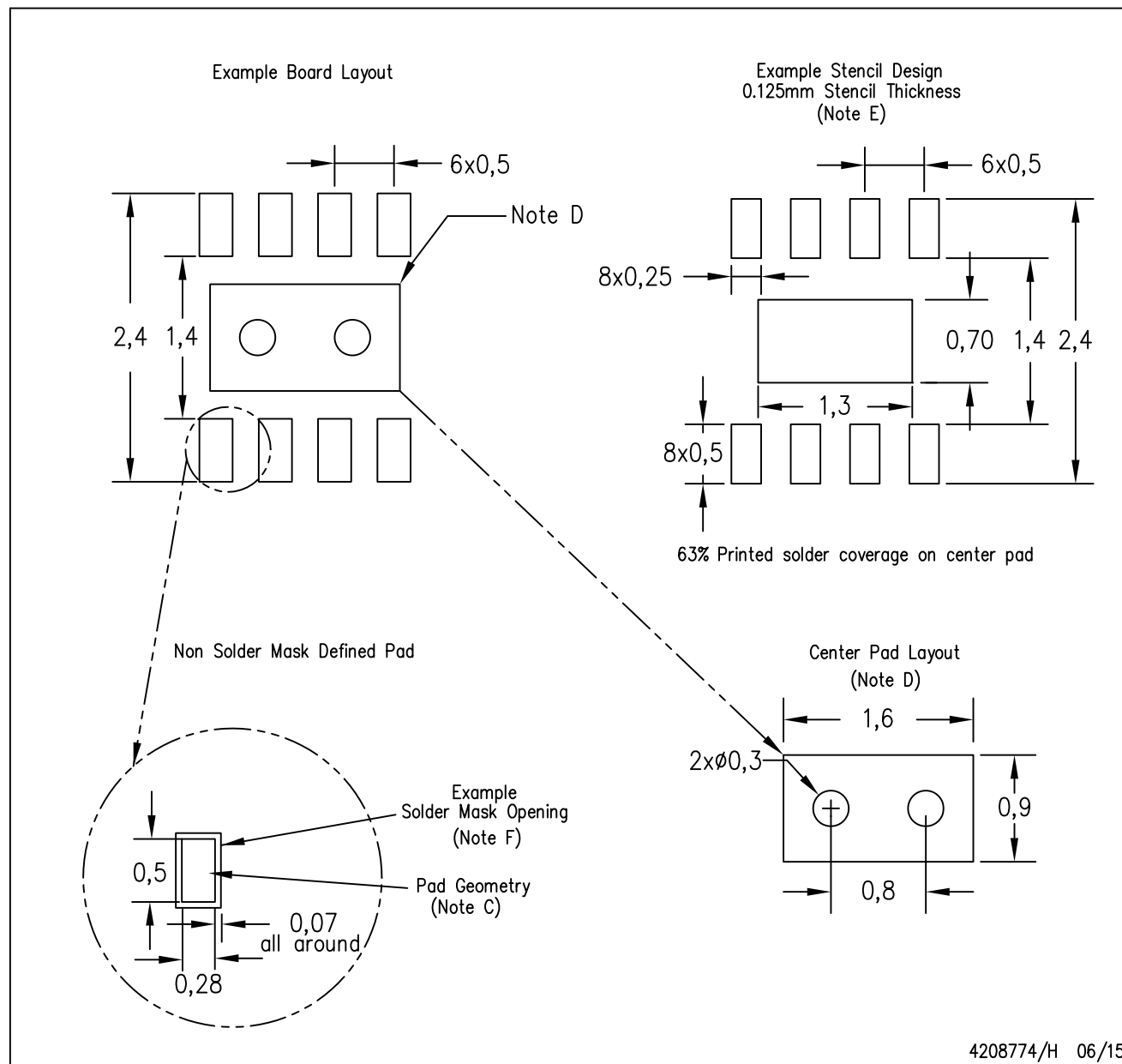
Exposed Thermal Pad Dimensions

4208347/I 06/15

NOTE: All linear dimensions are in millimeters

DSG (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at [www.ti.com](http://www.ti.com) <<http://www.ti.com>>.
  - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - F. Customers should contact their board fabrication site for solder mask tolerances.

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